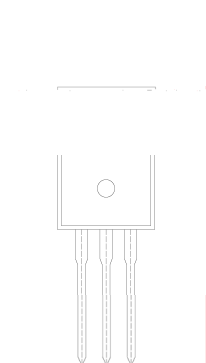


TO-220S

Ultrafast Recovery Diode in a TO-220S Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.



PIN1 Anode

PIN 2 Cathode

PIN 3 Anode

PIN 4 NC

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Rectified Forward Current	I_F	2×10	A
Non Repetitive Peak Surge Current	I_{FSM}	120	A
Thermal Resistance Junction to Case	$R_{\theta JC}$	2.9	/W
Storage Temperature Range	T_j T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=2A$ $T_c=25$		0.79		V
		$I_F=2A$ $T_c=125$		0.65		V
		$I_F=10A$ $T_c=25$		0.95	1.0	V
		$I_F=10A$ $T_c=125$		0.84	0.9	V
Instantaneous Reverse Current	I_R Note 1	$V_R=200V$ $T_a=25$			10	μA
		$V_R=200V$ $T_a=125$			150	μA
Reverse Recovery Time	t_{rr}	$I_R=1.0A$ $I_{RR}=0.25A$ $I_F=0.5A$			35	ns

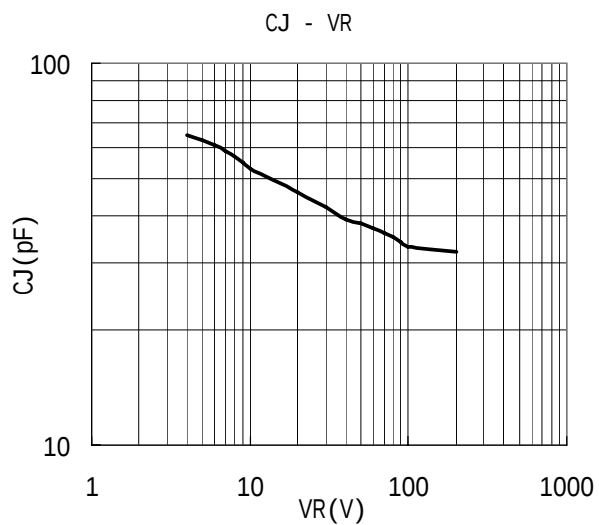
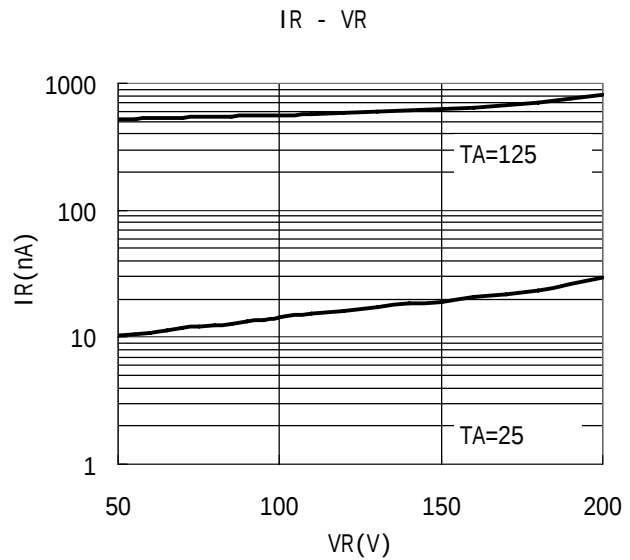
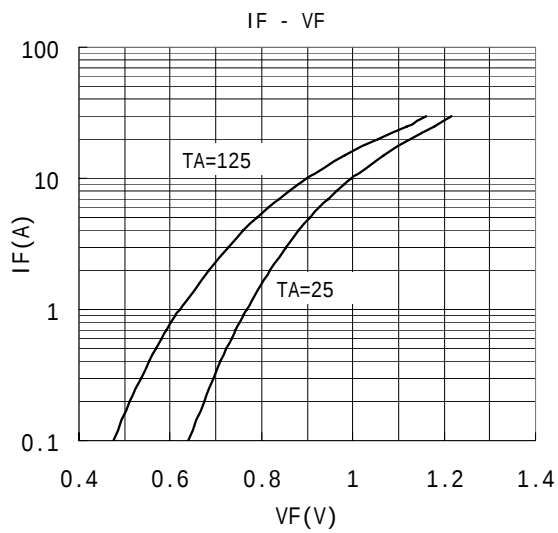
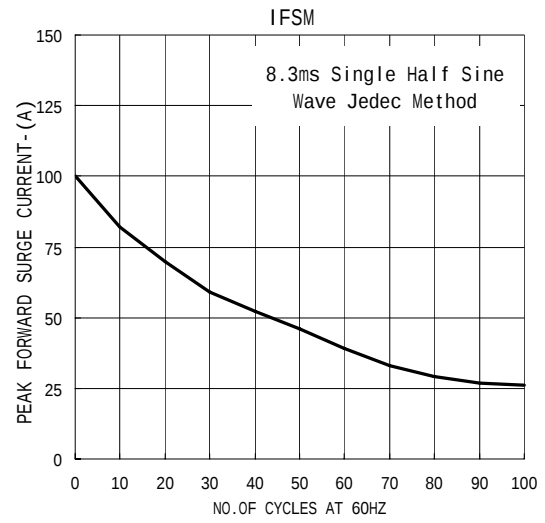
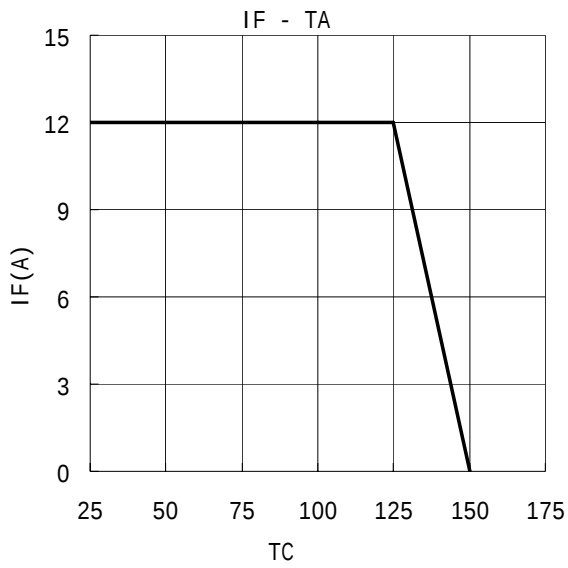
/Notes

1.
effect.

2.
single chip

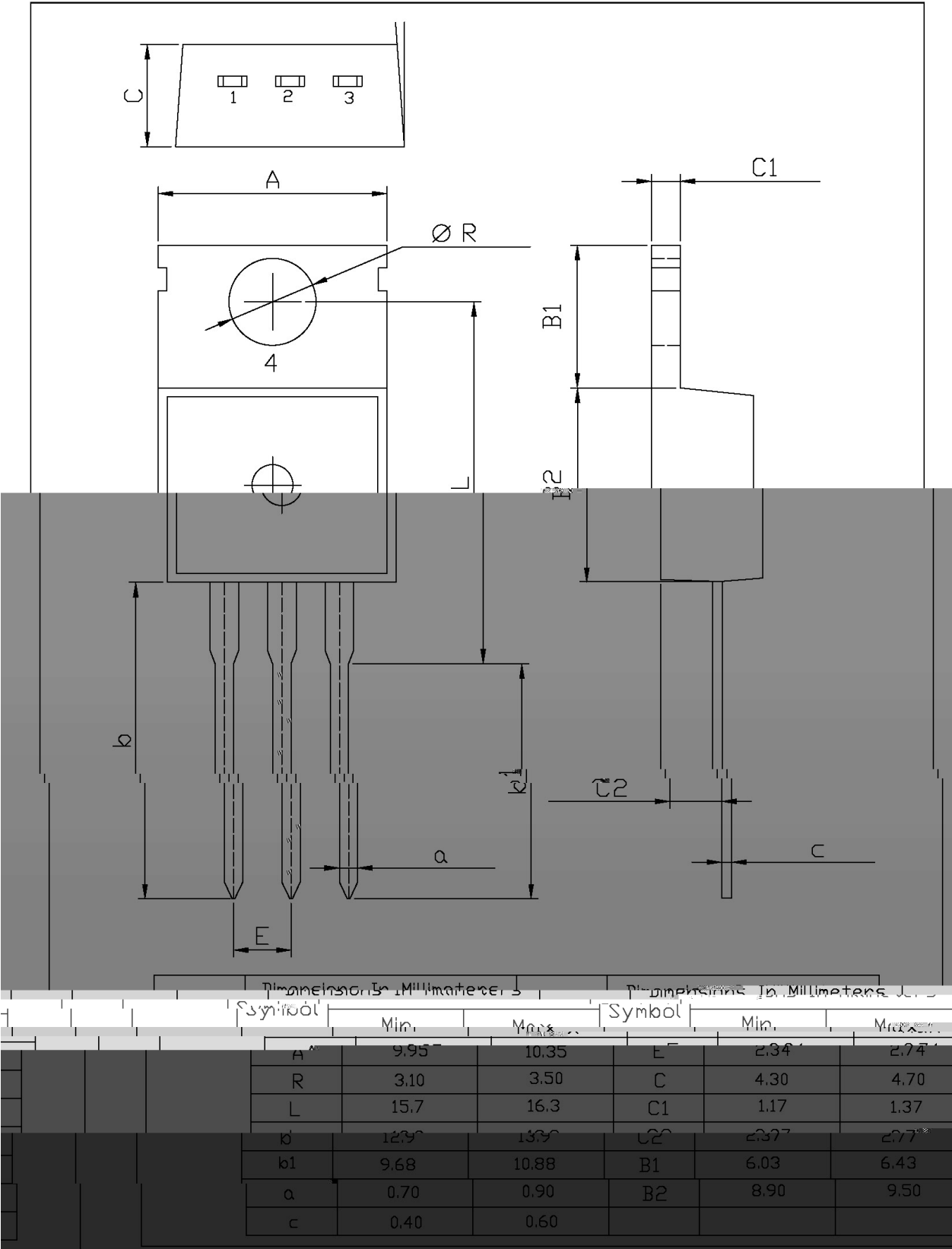
/Short duration pulse test used to minimize self-heating

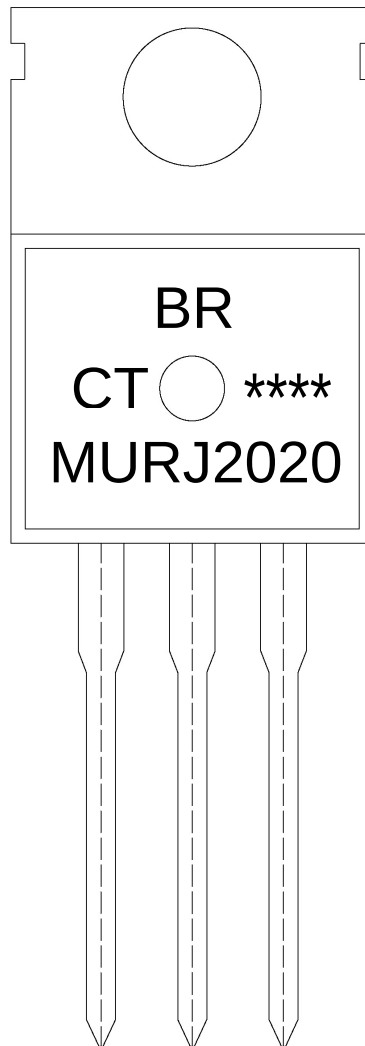
/ Unless otherwise noted, values for the parameters of a



TD-220S

Unit: mm





BR

MURJ2020

CT:

Note:

BR:

Company Code

MURJ2020

Product Type.

CT:

Internal Structure

****:

Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-220S	50	20	1000	5	5000	532×31.4×5.5	555×164×50	575×290×180